General description

General Application Schottky barrier rectifier, encapsulated in a DFN1006-2L leadless ultra small Surface-Mounted Device (SMD) plastic package.

Features and benefits

- Average forward current: $I_{F(AV)} \leqslant$ 200 mA
- Reverse voltage: $V_R \leqslant$ 40 V
- Low forward voltage: $V_F \leqslant$ 350 mV @10mA
- Low reverse current: $I_R \leqslant$ 10 μA
- Leadless ultra small SMD plastic package
- We declare that the material of product compliance with RoHS requirements and Halogen Free

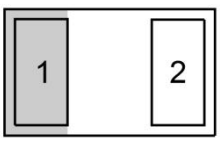
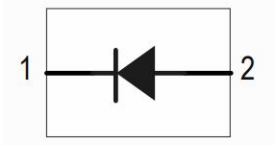
Application information

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

Ordering information

Device	Package	Marking	Packaging
PSB521BS-40	DFN1006-2L	F	10000/Tape & Reel

Schematic & Pin configuration

Simplified outline	Graphic symbol
	

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Maximum Ratings (T_A = 25 °C, unless otherwise specified)

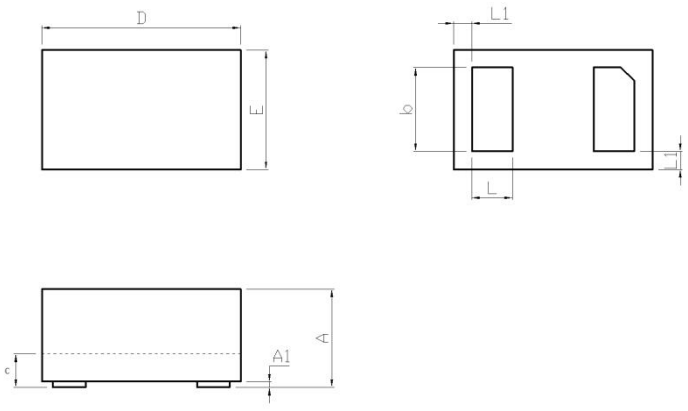
Parameter	Symbol	Value	Unit
DC reverse voltage	V_R	40	V
Average rectifierd forward current	I_O	200	mA
Forward current surge peak(60Hz · 1cyc)	I_{FSM}	500	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

Electrical Characteristics (T_A = 25 °C, unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Condition
Forward voltage	V_F	-- --	-- --	0.35 0.40	V	(IF=10mA) (IF=20mA)
Reverse current	I_R	--	--	10	uA	V_R=10V

Package Outline Dimensions

DFN1006-2L



SYMBOL	Dimensions In Millimet	
	MIN	MAX
A	0.46	0.50
A1	0	0.05
b	0.45	0.55
c	0.1	0.14
D	0.95	1.05
E	0.55	0.65
L	0.20	0.30
L1	0.035	0.065
h	0.07	0.17

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